

Please check that this question paper contains 9 questions and 2 printed pages within first ten minutes.

[Total No. of Questions: 09]

[Total No. of Pages: 02]

Uni. Roll No. ....

Program: B.Tech. (ECE)

Semester: 3

MORNING

Name of Subject: Electronic Devices

09 MAY 2023

Subject Code: PCEC-101

Paper ID: 16031

Scientific calculator is Allowed.

**Detail of allowed codes/charts/tables etc. Not Required.**

**Time Allowed: 03 Hours**

**Max. Marks: 60**

**NOTE:**

- 1) Parts A and B are compulsory.
- 2) Part-C has Two Questions Q8 and Q9. Both are compulsory, but with internal choice.
- 3) Any missing data may be assumed appropriately

**Part – A**

**[Marks: 02 each]**

**Q1:**

- a) Compare n-type and p-type semiconductors.
- b) Define stability factor of transistors.
- c) Draw the current-voltage characteristics of Tunnel diode.
- d) Explain h-parameters of a Common Base Transistor configuration and also, mention their units.
- e) If a transistor has  $\alpha=0.95$ , determine value of  $\beta$ .
- f) The intrinsic carrier concentration of Silicon is  $1.5 \times 10^{10} \text{cm}^{-3}$  at 300K. If after doping, the electron concentration is  $10^{15} \text{cm}^{-3}$ , determine the hole concentration.

**Part – B**

**[Marks: 04 each]**

Q2: Explain the working of Zener diode as a voltage regulator.

Q3: Illustrate the process of carrier generation and recombination in semiconductors.

Q4: Explain fixed bias stabilization technique for transistors.

Q5: Examine the role of amplification factor, transconductance and drain resistance in FET performance.

Q6: Determine  $V_{CE}$  and  $I_C$  in the voltage-divider bias transistor circuit. Assume  $\beta = 100$  and  $I_E \approx I_C$ .  $R_1 = 10 \text{ k}\Omega$ ,  $R_2 = 5.6 \text{ k}\Omega$ ,  $R_C = 1 \text{ k}\Omega$ ,  $R_E = 560 \Omega$ ,  $V_{CC} = 10 \text{V}$ .

Q7: A JFET has given parameters:  $I_{DSS} = 32 \text{ mA}$ ,  $V_{GS(off)} = -8\text{V}$ ,  $V_{GS} = -4.5\text{V}$ . Determine the value of drain current.

MORNING  
09 MAY 2023

Part – C

[Marks: 12 each]

Q8: Solve for the efficiency of half wave rectifier and full wave rectifier in ideal case.

OR

Explain the input and output characteristics of NPN Transistor in Common Emitter Configuration.

Q9: Distinguish between JFETs and MOSFETs. Also, explain drain characteristics, transfer characteristics and applications of MOSFETs.

OR

Discuss Hybrid-Pi Common Emitter Transistor Model with neat diagram and explanation of associated parameters.

\*\*\*\*\*